## MMBTSC3356W

# **NPN Silicon Epitaxial Planar Transistor**

for microwave low noise amplifier at VHF, UHF and CATV band.



The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.

1.Base 2.Emitter 3.Collector SOT-323 Plastic Package

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	V <sub>CBO</sub>	20	V	
Collector Emitter Voltage	V <sub>CEO</sub>	12	V	
Emitter Base Voltage	$V_{EBO}$	3	V	
Collector Current	I <sub>C</sub>	100	mA	
Power Dissipation	P <sub>tot</sub>	200	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Ts	- 65 to + 150	°C	

### Characteristics at T<sub>amb</sub> = 25 °C

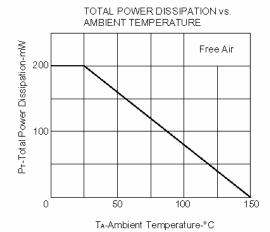
Parameter		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V <sub>CE</sub> = 10 V, I <sub>C</sub> = 20 mA Current Gain Group	Q	$h_{FE}$	50	-	100	-
	R	$h_{FE}$	80	-	160	-
	S	$h_{FE}$	125	-	250	-
Collector Cutoff Current at V <sub>CB</sub> = 10 V		I <sub>CBO</sub>	-	-	1	μA
Emitter Cutoff Current at V <sub>EB</sub> = 1 V		I <sub>EBO</sub>	-	-	1	μA
Gain Bandwidth Product at $V_{CE}$ = 10 V, $I_C$ = 20 mA		$f_{T}$	ı	7	-	GHz
Feed-Back Capacitance at V <sub>CB</sub> = 10 V, f = 1 MHz		C <sub>re</sub> <sup>1)</sup>	-	0.55	1	pF
Insertion Power Gain at $V_{CE}$ = 10 V, $I_C$ = 20 mA, f = 1 GHz		S <sub>21e</sub>   <sup>2</sup>	-	11.5	-	dB
Noise Figure at $V_{CE}$ = 10 V, $I_C$ = 7 mA, f = 1 GHz		NF	-	1.1	2	dB

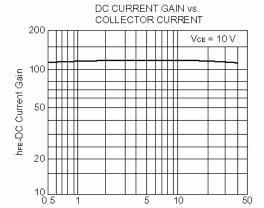
<sup>&</sup>lt;sup>1)</sup> The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.



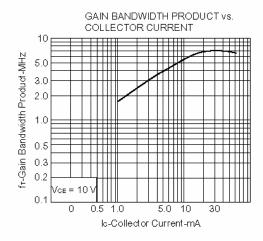


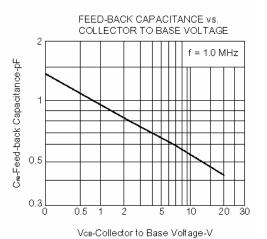
#### TYPICAL CHARACTERISTICS (TA = 25 °C)



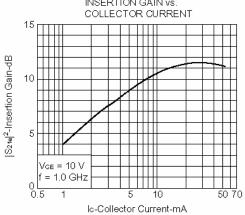


lc-Collector Current-mA

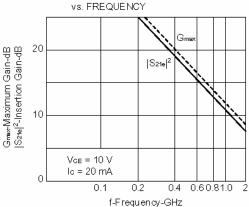








INSERTION GAIN, MAXIMUM GAIN







(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)





